



Silicon Carbide (SiC)

MCC's silicon carbide semiconductors deliver fast switching speed, low forward drop, and temperature stability, enabling a range of high-power and high-voltage applications. Our selection of SiC Schottky barrier diodes and SiC MOSFETs provide ruggedness, reliability, and wider bandgap, making them ideal for renewable energy systems and industrial automation.

Silicon Carbide (SiC)



PRODUCT

Silicon Carbide (SiC)



APPLICATION

Silicon Carbide (SiC)



Automotive SiC MOSFETs

Part Number	Package	Channel	Drain-Source Voltage	Drain Current	Drain-Source On-Resistance $R_{DS(ON)}$		Gate Source Voltage	Gate Threshold Voltage	Gate Threshold Voltage	Single Pulse Avalanche Energy	Pulsed Drain Current	Power Rating	Input Capacitance	Operating Junction Temperature
			V_{DS} (V)	I_D (A)	Max (m Ω)	@ V_{GS} (V)	V_{GS} (V)	$V_{GS(th)}$ (V) (Min)	$V_{GS(th)}$ (V) (Max)	E_{AS} (mJ)	I_{DM} (A)	P_D (W)	C_{iss} (pF)	T_J (°C)
SICW033N120Y4HE3	TO-247-4	N	1200	48	44	15	-8/+19	2	4	500	120	333	3456	175

※ Pre-Release ※

Part Number	Package	Channel	Drain-Source Voltage	Drain Current	Drain-Source On-Resistance $R_{DS(ON)}$		Gate Source Voltage	Gate Threshold Voltage	Gate Threshold Voltage	Single Pulse Avalanche Energy	Pulsed Drain Current	Power Rating	Input Capacitance	Operating Junction Temperature
			V_{DS} (V)	I_D (A)	Max (m Ω)	@ V_{GS} (V)	V_{GS} (V)	$V_{GS(th)}$ (V) (Min)	$V_{GS(th)}$ (V) (Max)	E_{AS} (mJ)	I_{DM} (A)	P_D (W)	C_{iss} (pF)	T_J (°C)
SICWZ025N120G3Q	TO-247-4	N	1200	80	30	18	-8/+22	2	4	1100	178	365	4710	175
SICW025N120G3Q	TO-247AB	N	1200	80	30	18	-8/+22	2	4	1100	178	365	4710	175

Automotive SBDs

Part Number	Package	Peak Repetitive Reverse Voltage	Average Forward Current	Peak Forward Surge Current	Forward Voltage	At Rated Forward Current	Reverse Voltage Leakage Current	Maximum DC Blocking Voltage	Power Dissipation	Operating Junction Temperature
		V_{RRM} (V)	$I_{F(AV)}$ (A)	I_{FSM} (A)	V_F (V)	I_F (A)	I_R (uA)	V_R (V)	P_D (mW)	T_J (°C)
SICB2065XG5MQ	D2-PAK	650	20	380	1.3	20	25	650	250	175
SICX0165G4JQ	SMA	650	1	75	1.3	1	0.5	650	16.4	175
SICU02120G4JQ	DPAK	1200	2	20	1.6	2	20	1200	42	175
SICU05120G4JQ	DPAK	1200	5	40	1.6	5	25	1200	89	175
SICU10120XG4JQ	DPAK	1200	10	85	1.55	10	20	1200	156	175
SIC10120G4JQ	TO-220AC	1200	10	85	1.55	10	25	1200	130	175

※ Pre-Release ※

Part Number	Package	Peak Repetitive Reverse Voltage	Average Forward Current	Peak Forward Surge Current	Forward Voltage	At Rated Forward Current	Reverse Voltage Leakage Current	Maximum DC Blocking Voltage	Power Dissipation	Operating Junction Temperature
		V_{RRM} (V)	$I_{F(AV)}$ (A)	I_{FSM} (A)	V_F (V)	I_F (A)	I_R (uA)	V_R (V)	P_D (mW)	T_J (°C)
SICB2065G4JQ	D2-PAK	650	20	135	1.6	20	25	650	130	175
SICB2065XG4JQ	D2-PAK	650	20	135	1.6	20	25	650	130	175
SICU0465G4JQ	DPAK	650	4	28	1.65	4	20	650	57	175
SICU0465XG4JQ	DPAK	650	4	28	1.65	4	20	650	57	175
SICU0865XG4JQ	DPAK	650	8	75	1.6	8	25	650	119	175
SICU1065G4JQ	DPAK	650	10	75	1.6	10	25	650	119	175
SICU1065XG4JQ	DPAK	650	10	75	1.6	10	25	650	119	175
SICF0465G4JQ	ITO-220AC	650	4	28	1.65	4	20	650	25	175
SIC0465G4JQ	TO-220AC	650	4	28	1.65	4	25	650	56	175
SIC3065G4JQ	TO-220AC	650	30	200	1.58	30	25	650	197	175
SICW2065DG4JQ	TO-247AB	650	20	75	1.6	10	25	650	227	175
SICW4065DG4JQ	TO-247AB	650	40	135	1.6	20	25	650	333	175
SICW6065DG4JQ	TO-247AB	650	60	200	1.58	30	25	650	468	175
SICWT1065G4JQ	TO-247AD	650	10	75	1.6	10	25	650	111	175
SICWT2065G4JQ	TO-247AD	650	20	135	1.6	20	25	650	168	175
SICWT3065G4JQ	TO-247AD	650	30	200	1.58	30	25	650	238	175
SICF02120G4JQ	ITO-220AC	1200	2	20	1.6	2	20	1200	23.8	175
SIC02120G4JQ	TO-220AC	1200	2	20	1.6	2	20	1200	47.5	175

Silicon Carbide (SiC)

SiC MOSFETs

Part Number	Package	Channel	Drain-Source Voltage	Drain Current	Drain-Source On-Resistance $R_{DS(ON)}$		Gate Source Voltage	Gate Threshold Voltage	Gate Threshold Voltage	Single Pulse Avalanche Energy	Pulsed Drain Current	Power Rating	Input Capacitance	Operating Junction Temperature
			V_{DS} (V)	I_D (A)	Max (m Ω)	@ V_{GS} (V)	V_{GS} (V)	$V_{GS(th)}$ (V)	$V_{GS(th)}$ (V)	E_{AS} (mJ)	I_{DM} (A)	P_D (W)	C_{iss} (pF)	T_j (°C)
SICW080N120Y	TO-247	N	1200	38	85	18	-8/+22	2.3	3.6	-	80	220	890	175
SICW080N120Y4	TO-247-4	N	1200	39	85	18	-8/+22	2.3	3.6	-	80	223	890	175
SICW028N120A4	TO-247-4	N	1200	80	35	18	-5/+22	1.5	3	1620	320	375	3570	175
SICW021N120P4	TO-247-4L	N	1200	100	29.4	18	-10/+22	2	4.5	-	250	469	3741	175
SICW025N120Y	TO-247AB	N	1200	80	40	18	-8/+22	2	4	-		365	4710	175
SICW021N120P	TO-247AB	N	1200	100	29.4	18	-10/+22	2	4.5	-	250	469	3741	175
SICBG160N120A	TO-263-7L	N	1200	18	160	18	-5/+22	1.5	3	216	72	116	780	175
SICW1000N170A	TO-247AB	N	1700	3	1370	18	-5/+25	2.5	4.5	-	12	69	124	150
SICW400N170A	TO-247AB	N	1700	6	550	18	-5/+25	2	4.5	259	24	125	333	175
SICW1000N170Y	TO-247AB	N	1700	6.8	1200	20	-10/+27	2	4	150	21	100	227	175

SiC MOSFETs

※ Pre-Release ※

Part Number	Package	Channel	Drain-Source Voltage	Drain Current	Drain-Source On-Resistance $R_{DS(ON)}$		Gate Source Voltage	Gate Threshold Voltage	Gate Threshold Voltage	Single Pulse Avalanche Energy	Pulsed Drain Current	Power Rating	Input Capacitance	Operating Junction Temperature
			V_{DS} (V)	I_D (A)	Max (mΩ)	@ V_{GS} (V)	V_{GS} (V)	$V_{GS(th)}$ (V) (Min)	$V_{GS(th)}$ (V) (Max)	E_{AS} (mJ)	I_{DM} (A)	P_D (W)	C_{iss} (pF)	T_J (°C)
SICT025N075G3	T2PAK	N	750	85	27	18	-8/+22	2	4	975	265	230	4121	175
SICT035N075G3	T2PAK	N	750	62	33	18	-8/+22	2	4	964	230	205	3465	175
SIC070N075G3	TO-220AB	N	750	55	70	18	-8/+22	2	4	410	130	170	1598	175
SICWZ025N075G3	TO-247-4	N	750	107	27	18	-8/+22	2	4	975	265	365	4121	175
SICWZ035N075G3	TO-247-4	N	750	82	33	18	-8/+22	2	4	964	230	300	3465	175
SICWZ050N075G3	TO-247-4	N	750	68	52	18	-8/+22	2	4	627	145	230	2542	175
SICWZ070N075G3	TO-247-4	N	750	55	70	18	-8/+22	2	4	410	130	175	1598	175
SICW025N075G3	TO-247AB	N	750	107	35	18	-8/+22	2	4	975	265	365	4121	175
SICW035N075G3	TO-247AB	N	750	82	33	18	-8/+22	2	4	964	230	300	3465	175
SICW050N075G3	TO-247AB	N	750	68	52	18	-8/+22	2	4	627	145	230	2542	175
SICW070N075G3	TO-247AB	N	750	55	70	18	-8/+22	2	4	410	130	175	1598	175
SICTL025N075G3	TOLL-8L-KS	N	750	90	27	18	-8/+22	2	4		265	258	4121	175
SICWZ025N120G3	TO-247-4	N	1200	80	30	18	-8/+22	2	4	1100	178	365	4710	175
SICWZ040N120G3	TO-247-4	N	1200	67	42	18	-8/+22	2	4	870	180	333	3362	175
SICWZ060N120G3	TO-247-4	N	1200	46	66	18	-8/+22	2	4	534	90	214	2138	175
SICWZ080N120G3	TO-247-4	N	1200	35	92	18	-8/+22	2	4	402	85	175	1665	175
SICWZ120N120G3	TO-247-4	N	1200	21	145	18	-8/+22	2	4	227	57	125	1066	175
SICW040N120G3	TO-247AB	N	1200	67	42	18	-8/+22	2	4	870	180	333	3362	175
SICW060N120G3	TO-247AB	N	1200	46	66	18	-8/+22	2	4	534	90	214	2138	175
SICW080N120G3	TO-247AB	N	1200	35	92	18	-8/+22	2	4	402	85	175	1665	175
SICW120N120G3	TO-247AB	N	1200	24	145	18	-8/+22	2	4	230	57	125	1066	175
SICW160N120G3	TO-247AB	N	1200	19	200	18	-8/+22	2	4	120	43	95	836	175
SICW320N120G3	TO-247AB	N	1200	12	377	18	-8/+22	2	4	90	17	92.6	470	175
SICBG025N120G3	TO-263-7L(A)	N	1200	64	30	18	-8/+22	2	4	1100	172	211	4710	175
SICBG040N120G3	TO-263-7L(A)	N	1200	57	42	18	-8/+22	2	4	870	172	234	3362	175
SICBG080N120G3	TO-263-7L(A)	N	1200	29	92	18	-8/+22	2	4	402	85	116	1665	175
SICBG120N120G3	TO-263-7L(A)	N	1200	21	145	18	-8/+22	2	4	230	57	104	1066	175
SICBG160N120G3	TO-263-7L(A)	N	1200	18.5	200	18	-8/+22	2	4	120	43	98	836	175
SICBG320N120G3	TO-263-7L(A)	N	1200	11	377	18	-8/+22	2	4	90	17	71	470	175

Silicon Carbide (SiC)

SiC Schottky Barrier Diodes

Part Number	Package	Peak Repetitive Reverse Voltage	Average Forward Current	Peak Forward Surge Current	Forward Voltage	At Rated Forward Current	Reverse Voltage Leakage Current	Maximum DC Blocking Voltage	Power Dissipation	Operating Junction Temperature
		V_{RRM} (V)	$I_{F(AV)}$ (A)	I_{FSM} (A)	V_F (V)	I_F (A)	I_R (uA)	V_R (V)	P_D (mW)	T_J (°C)
SICB0660Y	D2-PAK	650	6	175	1.5	6	25	650	84	175
SICB0665G5M	D2-PAK	650	6	65	1.55	6	25	650	75	175
SICB0860P	D2-PAK	650	8	70	1.55	8	25	650	136	175
SICB1060P	D2-PAK	650	10	80	1.55	10	25	650	136	175
SICB1065G4J	D2-PAK	650	10	75	1.6	10	25	650	107	175
SICB2060Y	D2-PAK	650	20	160	1.55	20	25	650	144	175
SICB2065G4J	D2-PAK	650	20	135	1.6	20	25	650	130	175
SICB2065XG5M	D2-PAK	650	20	380	1.3	20	25	650	250	175
SICB5060XY	D2-PAK	650	50	380	1.6	50	25	650	375	175
SIC0860PL8	DFN8080A	650	8	80	1.55	8	25	650	70	175
SIC1060PL8	DFN8080A	650	10	80	1.55	10	25	650	70	175
SICU0260B	DPAK	650	2	22	1.6	2	10	650	60	175
SICU0460B	DPAK	650	4	34	1.8	4	15	650	60	175
SICU0465G4J	DPAK	650	4	28	1.65	4	20	650	57	175
SICU0465XG4J	DPAK	650	4	28	1.65	4	20	650	57	175
SICU0660P	DPAK	650	6	65	1.5	6	25	650	100	175
SICU0860P	DPAK	650	8	70	1.55	8	25	650	132	175
SICU1060P	DPAK	650	10	80	1.55	10	25	650	132	175
SICU1060XY	DPAK	650	10	70	1.55	10	25	650	132	175
SICU1065G4J	DPAK	650	10	75	1.6	10	25	650	119	175
SICU1065XG4J	DPAK	650	10	75	1.6	10	25	650	119	175
SICF0465Y	ITO-220AC	650	4	28	1.65	4	20	650	25	175
SICF0660Y	ITO-220AC	650	6	65	1.5	6	25	650	31	175
SICF0860P	ITO-220AC	650	8	70	1.55	8	25	650	43	175
SICF1060P	ITO-220AC	650	10	80	1.55	10	25	650	43	175
SICF2060Y	ITO-220AC	650	20	160	1.55	20	25	650	47	175
SIC0260Y	TO-220AC	650	2	20	1.6	2	10	650	45	175
SIC0465Y	TO-220AC	650	4	28	1.65	4	25	650	56	175
SIC0660P	TO-220AC	650	6	65	1.5	6	25	650	84	175
SIC0665G4J	TO-220AC	650	6	75	1.4	6	25	650	110	175
SIC0665G5M	TO-220AC	650	6	60	1.55	6	25	650	80	175
SIC0860P	TO-220AC	650	8	70	1.55	8	25	650	136	175
SIC0865G4J	TO-220AC	650	8	75	1.6	8	25	650	110	175
SIC1060P	TO-220AC	650	10	80	1.55	10	25	650	136	175
SIC1065G4J	TO-220AC	650	10	75	1.6	10	25	650	110	175
SIC1065G5M	TO-220AC	650	10	60	1.7	10	25	650	80	175
SIC2060Y	TO-220AC	650	20	160	1.55	20	25	650	170	175
SIC3065G4J	TO-220AC	650	30	200	1.6	30	25	650	197	175
SICPT2060DY	TO-247AB	650	20	70	1.55	20	25	650	112	175
SICPT2065DY	TO-247AB	650	20	75	1.6	10	25	650	227	175
SICW2065DG5M	TO-247AB	650	20	65	1.7	20	25	650	172	175
SICW3065DG5M	TO-247AB	650	30	160	1.6	15	25	650	267	175
SICPT4060DY	TO-247AB	650	40	160	1.55	40	25	650	365	175
SICW4065DG4J	TO-247AB	650	40	135	1.6	20	25	650	333	175

SiC Schottky Barrier Diodes

Part Number	Package	Peak Repetitive Reverse Voltage	Average Forward Current	Peak Forward Surge Current	Forward Voltage	At Rated Forward Current	Reverse Voltage Leakage Current	Maximum DC Blocking Voltage	Power Dissipation	Operating Junction Temperature
		V_{RRM} (V)	$I_{F(AV)}$ (A)	I_{FSM} (A)	V_F (V)	I_F (A)	I_R (uA)	V_R (V)	P_D (mW)	T_J (°C)
SICW4065DG5M	TO-247AB	650	40	160	1.65	20	25	650	267	175
SICPT6065DY	TO-247AB	650	60	200	1.58	10	25	650	469	175
SICPT1060Y	TO-247AD	650	10	70	1.55	10	5	650	126	175
SICWT1065G4J	TO-247AD	650	10	75	1.6	10	25	650	111	175
SICPT2060Y	TO-247AD	650	20	160	1.55	20	25	650	187	175
SICPT2065Y	TO-247AD	650	20	135	1.6	20	25	650	168	175
SICPT3060Y	TO-247AD	650	30	180	1.65	30	25	650	187	175
SICWT3065G4J	TO-247AD	650	30	200	1.58	30	25	650	238	175
SICPT5060Y	TO-247AD	650	50	380	1.6	50	25	650	454	175
SICWT5065G5M	TO-247AD	650	50	380	1.7	50	25	650	288	175
SICB10120G4J	D2-PAK	1200	10	85	1.6	10	25	1200	136	175
SICB10120XG4J	D2-PAK	1200	10	85	1.6	10	25	1200	136	175
SICB10120Y	D2-PAK	1200	10	85	1.54	10	13	1200	158	175
SICB10120YA	D2-PAK	1200	10	85	1.54	10	13	1200	158	175
SICB20120Y	D2-PAK	1200	20	160	1.55	20	25	1200	333	175
SICU02120B	DPAK	1200	2	27	1.7	2	10	1200	63	175
SICU02120G4J	DPAK	1200	2	20	1.6	2	20	1200	42	175
SICU05120G4J	DPAK	1200	5	40	1.6	5	25	1200	89	175
SICU10120Y	DPAK	1200	10	85	1.54	10	13	1200	189	175
SICF02120Y	ITO-220AC	1200	2	20	1.6	2	20	1200	23.8	175
SICF10120Y	ITO-220AC	1200	10	85	1.54	10	13	1200	36	175
SIC02120Y	TO-220AC	1200	2	20	1.6	2	20	1200	47.5	175
SIC05120G4J	TO-220AC	1200	5	40	1.6	5	25	1200	82	175
SIC10120G4J	TO-220AC	1200	10	85	1.55	10	25	1200	130	175
SIC10120Y	TO-220AC	1200	10	85	1.54	10	13	1200	170	175
SIC15120Y	TO-220AC	1200	15	140	1.45	15	25	1200	240	175
SIC20120Y	TO-220AC	1200	20	160	1.55	20	25	1200	241	175
SICW10120DG4J	TO-247AB	1200	10	40	1.6	5	25	1200	164	175
SICPT20120DY	TO-247AB	1200	20	85	1.54	20	13	1200	267	175
SICW20120DG4J	TO-247AB	1200	20	85	1.6	10	25	1200	288	175
SICPT30120DY	TO-247AB	1200	30	144	1.45	30	25	1200	319	175
SICW30120DG4J	TO-247AB	1200	30	160	1.45	15	25	1200	454	175
SICW30120DG5M	TO-247AB	1200	30	180	1.6	15	25	1200	265	175
SICPT40120DY	TO-247AB	1200	40	160	1.55	40	25	1200	319	175
SICW40120DG4J	TO-247AB	1200	40	160	1.6	20	25	1200	454	175
SICW40120DG5M	TO-247AB	1200	40	180	1.7	20	25	1200	365	175
SICW60120DG4J	TO-247AB	1200	60	235	1.58	30	25	1200	577	175
SICPT10120Y	TO-247AD	1200	10	85	1.54	10	13	1200	266	175
SICPT15120Y	TO-247AD	1200	15	144	1.45	15	25	1200	319	175
SICWT15120G5M	TO-247AD	1200	15	180	1.6	15	25	1200	187	175
SICPT20120Y	TO-247AD	1200	20	160	1.55	20	25	1200	319	175
SICWT20120G4J	TO-247AD	1200	20	160	1.6	20	25	1200	230	175
SICWT20120G6M	TO-247AD	1200	20	200	1.6	20	25	1200	205	175
SICPT30120YA	TO-247AD	1200	30	225	1.58	30	30	1200	416	175

Silicon Carbide (SiC)

SiC Schottky Barrier Diodes

Part Number	Package	Peak Repetitive Reverse Voltage	Average Forward Current	Peak Forward Surge Current	Forward Voltage	At Rated Forward Current	Reverse Voltage Leakage Current	Maximum DC Blocking Voltage	Power Dissipation	Operating Junction Temperature
		V_{RRM} (V)	I_{FAV} (A)	I_{FSM} (A)	V_f (V)	I_f (A)	I_r (uA)	V_R (V)	P_D (mW)	T_j (°C)
SICPT30120YB	TO-247AD	1200	30	250	1.75	30	33	1200	326	175
SICWT30120G4J	TO-247AD	1200	30	235	1.6	30	25	1200	294	175
SICPT40120Y	TO-247AD	1200	40	300	1.6	40	20	1200	573	175
SICPT40120YA	TO-247AD	1200	40	280	1.58	40	38	1200	440	175
SICWT40120G6M	TO-247AD	1200	40	330	1.65	40	25	1200	348	175
SICPT60120Y	TO-247AD	1200	60	471	1.62	60	30	1200	789	175
SICWT60120G6M	TO-247AD	1200	60	470	1.65	60	25	1200	500	175
SICPT25170P	TO-247AD	1700	25	191	1.8	25	100	1700	294	175

※ Pre-Release ※

Part Number	Package	Peak Repetitive Reverse Voltage	Average Forward Current	Peak Forward Surge Current	Forward Voltage	At Rated Forward Current	Reverse Voltage Leakage Current	Maximum DC Blocking Voltage	Power Dissipation	Operating Junction Temperature
		V_{RRM} (V)	I_{FAV} (A)	I_{FSM} (A)	V_f (V)	I_f (A)	I_r (uA)	V_R (V)	P_D (mW)	T_j (°C)
SICB1065G5M	D2-PAK	650	10	65	1.75	10	25	650	75	175
SICB2065XG4J	D2-PAK	650	20	135	1.6	20	25	650	130	175
SICB3065G4J	D2-PAK	650	30	190	1.6	30	25	650	130	175
SICB5065XG5M	D2-PAK	650	50	380	1.7	50	25	650	250	175
SICU0865XG4J	DPAK	650	8	75	1.6	8	25	650	119	175
SICU2065XG5M	DPAK	650	20	160	1.65	20	25	650	156	175
SIC0465G5M	TO-220AC	650	4	60	1.35	4	20	650	80	175
SIC2065G4J	TO-220AC	650	20	135	1.6	20	25	650	153	175
SIC1565G5M	TO-220AC	650	15	160	1.55	15	25	650	151	175
SIC2065G5M	TO-220AC	650	20	160	1.65	20	25	650	151	175
SICB20120G4J	D2-PAK	1200	20	160	1.55	20	25	1200	172	175
SICB20120XG4J	D2-PAK	1200	20	160	1.55	20	25	1200	172	175
SICF15120G5M	ITO-220AC	1200	15	150	1.6	15	25	1200	45	175
SIC08120G5M	TO-220AC	1200	8	80	1.65	8	25	1200	101	175
SIC15120G5M	TO-220AC	1200	15	180	1.6	15	25	1200	161	175
SIC20120G5M	TO-220AC	1200	20	180	1.7	20	25	1200	161	175
SICW40120G4J	TO-247AB	1200	40	260	1.58	40	25	1200	357	175
SICW80120DG4J	TO-247AB	1200	80	260	1.65	40	25	1200	714	175
SICW60120DG5M	TO-247AB	1200	60	320	1.6	30	25	1200	535	175
SICWT10120G4J	TO-247AD	1200	10	85	1.55	10	25	1200	145	175
SICWT20120G5M	TO-247AD	1200	20	180	1.7	20	25	1200	187	175
SICWT40120G4J	TO-247AD	1200	40	260	1.65	40	25	1200	357	175
SICWT30120G6M	TO-247AD	1200	30	290	1.65	30	25	1200	333	175
SICWT30120G5M	TO-247AD	1200	30	320	1.6	30	25	1200	277	175
SICWT60120G4J	TO-247AD	1200	60	390	1.6	60	25	1200	500	175
SICWT40120G5M	TO-247AD	1200	40	400	1.6	40	25	1200	300	175
SIC10170G5M	TO-220AC	1700	10	160	1.6	10	25	1700	208	175

SiC MOSFET Modules

※ Pre-Release ※

Part Number	Package	Channel	Drain-Source Voltage	Drain Current	Drain-Source On-Resistance $R_{DS(ON)}$		Gate Source Voltage	Gate Threshold Voltage	Gate Threshold Voltage	Diode Forward Voltage	Pulsed Drain Current	Power Rating	Input Capacitance	Operating Junction Temperature
			V_{DS} (V)	I_D (A)	Max (m Ω)	@ V_{GS} (V)	V_{GS} (V)	V_{GSEB} (V) (Min)	V_{GSEB} (V) (Max)	V_{SD} (mJ)	I_{DM} (V)	P_D (W)	C_{iss} (pF)	T_j (°C)
SICMC17D0N120G3H	C1	N	1200	180	9	18	-10/+22	2	4	5.3	280	430	8.471	175
SICSC2A4D0N120G3H	C2A	N	1200	400	5	18	-10/+22	2	4	1.51	630	1120	6.86	175

Silicon Carbide (SiC)

※ Pre-Release ※

SiC Schottky Diode Modules

Part Number	Package	Peak Repetitive Reverse Voltage	Average Forward Current	Peak Forward Surge Current	Forward Voltage	At Rated Forward Current	Reverse Voltage Leakage Current	Maximum DC Blocking Voltage	Power Dissipation	Operating Junction Temperature
		V_{RRM} (V)	I_{FAV} (A)	I_{FSM} (A)	V_F (V)	I_F (A)	I_R (uA)	V_R (V)	P_D (mW)	T_J (°C)
SICDFJ6X180065G4P	FJ	650	2X90	350	1.8	90	100	650	245	175
SICDST4X200065G5P	ST	650	2X100	680	1.7	100	100	650	265	175
SICDST6X120065G4P	ST	650	2X60	350	1.7	60	100	650	245	175
SICDST6X180065G4P	ST	650	2X90	680	1.7	90	100	650	265	175
SICDF212X480120G4Z	F2	1200	480	3240	1.7	480	300	1200	1400	175
SICDFJ2X60120G4P	FJ	1200	2X30	215	1.7	30	100	1200	155	175
SICDFJ4X120120G4P	FJ	1200	2X60	430	1.7	60	100	1200	250	175
SICDFJ4X80120G4P	FJ	1200	2X40	285	1.7	40	100	1200	225	175
SICDFJ6X200120G4P	FJ	1200	2X100	650	1.7	100	100	1200	305	175
SICDST2X60120G4P	ST	1200	2X30	215	1.7	30	100	1200	155	175
SICDST4X120120G4P	ST	1200	2X60	430	1.7	60	100	1200	250	175
SICDST4X80120G4P	ST	1200	2X40	285	1.7	40	100	1200	225	175
SICDST6X200120G4P	ST	1200	2X100	650	1.7	100	100	1200	305	175
SICRF210X150170G5D	F2	1700	150	1090	2	150	2500	1700	585	175
SICRFJ4X30170G5LV	FJ	1700	30	215	1.95	30	500	1700	185	175
SICRST4X80170G5P	ST	1700	2X40	405	1.8	40	100	1700	265	175